

ISC Silicon NPN Power Transistor

MJW21192

DESCRIPTION

- •DC Current Gain Specified up to 8.0 Amperes at Temperature
- High DC Current Gain h FE = 5(Min)@ I C = 8 Adc
- TO-3PN Package
- Complement to Type MJW21191
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

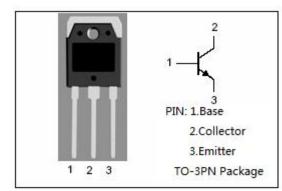
• Designed for power audio output,or high power drivers in audio amplifiers applications.

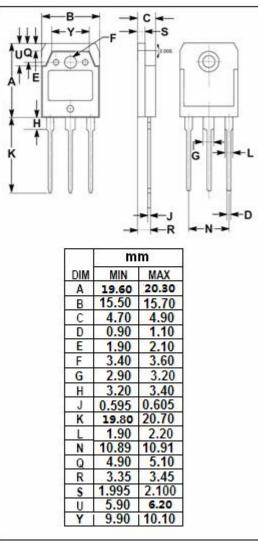
ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------------|
| V _{CBO} | Collector-Base Voltage | 150 | V |
| V_{CEO} | Collector-Emitter Voltage | 150 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| Ic | Collector Current-Continuous | 8 | Α |
| Ісм | Collector Current-Pulse | 16 | Α |
| lΒ | Base Current-Continuous | 2 | Α |
| Pc | Collector Power Dissipation @ T _C =25°C | 100 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| Tstg | Storage Temperature Range | -65~150 | $^{\circ}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|---|------|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | 0.65 | °C/W |
| R _{th j-a} | R _{th j-a} Thermal Resistance, Junction to Ambient | | °C/W |







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|------------------------|--------------------------------------|--|-----|------|-----|------------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 10mA ; I _B = 0 | 150 | | | V |
| V _{CE(sat)-1} | Collector-Emitter Saturation Voltage | I _C = 4A; I _B = 0.4A | | | 1.0 | V |
| V _{CE(sat)-2} | Collector-Emitter Saturation Voltage | I _C = 8A; I _B = 1.6A | | | 2.0 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = 4A; V _{CE} = 2V | | | 2.0 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 150V; I _E = 0 | | | 10 | μ А |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 150V; I _E = 0 | | | 100 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 10 | μА |
| h _{FE-1} | DC Current Gain | I _C = 4A ; V _{CE} = 2V | 15 | | 100 | |
| h _{FE-2} | DC Current Gain | I _C = 8A ; V _{CE} = 2V | 5 | | | |
| f⊤ | Current-Gain—Bandwidth Product | I _E = 1A; V _{CE} = 10V | 4 | | | MHz |

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